### Si3443BDV

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Vishay Siliconix



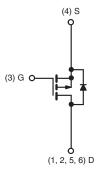
#### FEATURES

P-Channel 2.5 V (G-S) MOSFET

- TrenchFET<sup>®</sup> power MOSFET
- 100 % R<sub>g</sub> tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN



P-Channel MOSFET

Marking Code: 3B

| PRODUCT SUMMARY                                     |        |  |  |  |  |
|---|--------|--|--|--|--|
| V <sub>DS</sub> (V)                                 | -20    |  |  |  |  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = -4.5 V | 0.060  |  |  |  |  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = -2.7 V | 0.090  |  |  |  |  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = -2.5 V | 0.100  |  |  |  |  |
| Q <sub>g</sub> typ. (nC)                            | 6      |  |  |  |  |
| I <sub>D</sub> (A) <sup>a</sup>                     | -4.7   |  |  |  |  |
| Configuration                                       | Single |  |  |  |  |

| ORDERING INFORMATION            |                  |  |  |  |
|---------------------------------|------------------|--|--|--|
| Package                         | TSOP-6           |  |  |  |
| Lead (Pb)-free                  | Si3443BDV-T1-E3  |  |  |  |
| Lead (Pb)-free and halogen-free | Si3443BDV-T1-GE3 |  |  |  |

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted) |                        |                                   |             |    |  |
|--|------------------------|-----------------------------------|-------------|----|--|
| PARAMETER  | SYMBOL                 | LIMIT                             | UNIT        |    |  |
| Drain-source voltage   |                        | V <sub>DS</sub>                   | -20         |    |  |
| Gate-source voltage  | V <sub>GS</sub>        | ± 12                              | V           |    |  |
| Or attinuous durin comment (T 150 °O) a  | T <sub>A</sub> = 25 °C | - I <sub>D</sub>                  | -3.6        | ٥  |  |
| Continuous drain current (T <sub>J</sub> = 150 °C) <sup>a</sup>                  | T <sub>A</sub> = 70 °C |                                   | -2.8        |    |  |
| Pulsed drain current   |                        | I <sub>DM</sub>                   | -20         | А  |  |
| Continuous source current (diode conduction) <sup>a</sup>                        | ۱ <sub>S</sub>         | -0.9                              |             |    |  |
| Maximum power dissipation <sup>a</sup>   | T <sub>A</sub> = 25 °C | Р                                 | 1.1         | W  |  |
| Maximum power dissipation ~  | T <sub>A</sub> = 70 °C | P <sub>D</sub>                    | 0.7         | vv |  |
| Operating junction and storage temperature range                                 |                        | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 | °C |  |

| THERMAL RESISTANCE RATINGS               |              |                   |         |         |      |
|--|--------------|-------------------|---------|---------|------|
| PARAMETER                                |              | SYMBOL            | TYPICAL | MAXIMUM | UNIT |
| Maximum junction-to-ambient <sup>a</sup> | t ≤ 5 s      | R <sub>thJA</sub> | 50      | 62.5    | °C/W |
|  | Steady state |                   | 90      | 110     |      |
| Maximum junction-to-foot (drain)         | Steady state | R <sub>thJF</sub> | 30      | 36      |      |

Note

a. Surface mounted on FR4 board,  $t \leq 5 \mbox{ s}$ 



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| <b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |   |      |       |       |      |  |
|--|---------------------|---|------|-------|-------|------|--|
| PARAMETER  | SYMBOL              | TEST CONDITIONS   | MIN. | TYP.  | MAX.  | UNIT |  |
| Static   |                     |   |      |       |       |      |  |
| Gate threshold voltage   | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$                    | -0.6 | -     | -1.4  | V    |  |
| Gate-body leakage  | I <sub>GSS</sub>    | $V_{DS} = 0 V, V_{GS} = \pm 12 V$                           | -    | -     | ± 100 | nA   |  |
| Zero gate voltage drain current  | I                   | $V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$      | -    | -     | -1    | - uA |  |
| Zero gate voltage drain current  | I <sub>DSS</sub>    | $V_{DS}$ = -20 V, $V_{GS}$ = 0 V, $T_{J}$ = 70 °C           | -    | -     | -5    |      |  |
| On-state drain current <sup>a</sup>                                    | I <sub>D(on)</sub>  | $V_{DS} = -5 V, V_{GS} = -4.5 V$                            | -15  | -     | -     | А    |  |
|  |                     | $V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -4.7 \text{ A}$   | -    | 0.048 | 0.060 | Ω    |  |
| Drain-source on-state resistance <sup>a</sup>                          | R <sub>DS(on)</sub> | $V_{GS} = -2.7 \text{ V}, I_D = -3.8 \text{ A}$             | -    | 0.070 | 0.090 |      |  |
|  |                     | $V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -1 \text{ A}$     | -    | 0.080 | 0.100 |      |  |
| Forward transconductance <sup>a</sup>                                  | g <sub>fs</sub>     | $V_{DS} = -10 \text{ V}, \text{ I}_{D} = -4.7 \text{ A}$    | -    | 11    | -     | S    |  |
| Diode forward voltage <sup>a</sup>                                     | V <sub>SD</sub>     | $I_{\rm S}$ = -1.7 A, $V_{\rm GS}$ = 0 V                    | -    | -0.8  | -1.2  | V    |  |
| Dynamic <sup>b</sup>   |                     |   |      |       |       |      |  |
| Total gate charge  | Qg                  |   | -    | 6     | 9     |      |  |
| Gate-source charge   | Q <sub>gs</sub>     | $V_{DS}$ = - 10 V, $V_{GS}$ = - 4.5 V, $I_{D}$ = - 4.7 A    | -    | 1.4   | -     | nC   |  |
| Gate-drain charge  | Q <sub>gd</sub>     |   | -    | 1.9   | -     |      |  |
| Gate resistance  | R <sub>g</sub>      | f = 1 MHz   | 5    | 9.5   | 16.2  | Ω    |  |
| Turn-on delay time   | t <sub>d(on)</sub>  |   | -    | 22    | 35    |      |  |
| Rise time  | t <sub>r</sub>      | $V_{DD}$ = - 10 V, $R_L$ = 10 $\Omega$                      | -    | 35    | 55    |      |  |
| Turn-off delay time  | t <sub>d(off)</sub> | $I_D\cong$ - 1.0 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$ | -    | 45    | 70    | ns   |  |
| Fall time  | t <sub>f</sub>      |   | -    | 25    | 40    |      |  |
| Source-drain reverse recovery time                                     | t <sub>rr</sub>     | I <sub>F</sub> = - 1.7 A, dl/dt = 100 A/μs                  | -    | 25    | 50    |      |  |

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. Guaranteed by design, not subject to production testing

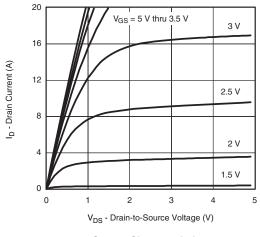
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



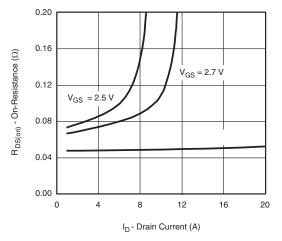
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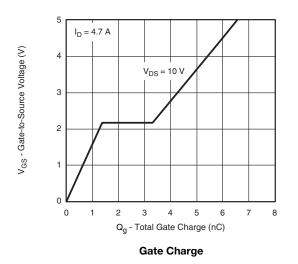
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

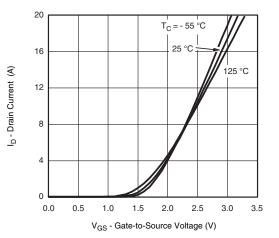


**Output Characteristics** 

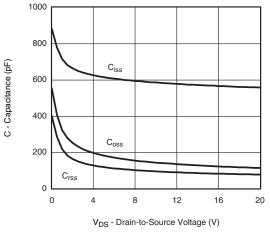


**On-Resistance vs. Drain Current** 

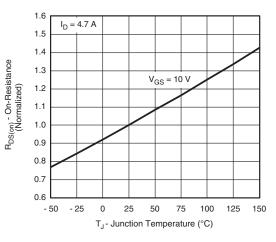




Transfer Characteristics



Capacitance



**On-Resistance vs. Junction Temperature** 

S-09.0660-Rev. C, 20-Apr-09

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Document Number: 72749

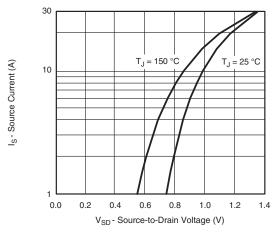
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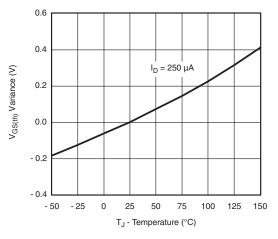
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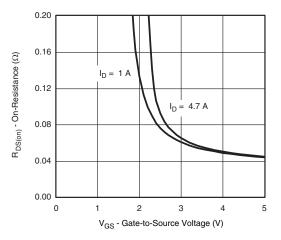
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



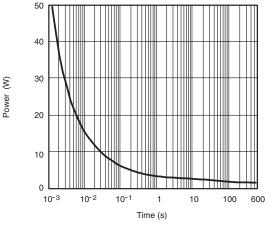
Source-Drain Diode Forward Voltage



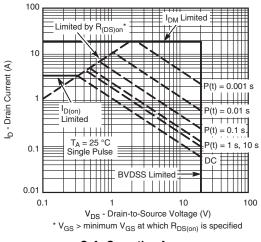




**On-Resistance vs. Gate-to-Source Voltage** 







Safe Operating Area

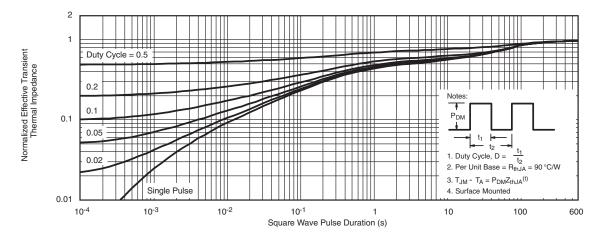
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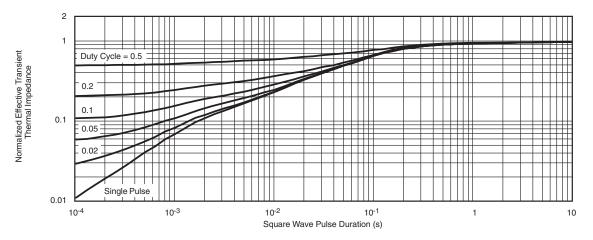


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72749.



Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



|   | MIL      | LIMETER  | RS   | INCHES     |           |       |
|---|----------|----------|------|------------|-----------|-------|
| Dim   | Min      | Nom      | Max  | Min        | Nom       | Max   |
| Α   | 0.91     | -        | 1.10 | 0.036      | -         | 0.043 |
| <b>A</b> <sub>1</sub>                       | 0.01     | -        | 0.10 | 0.0004     | -         | 0.004 |
| A <sub>2</sub>                              | 0.90     | -        | 1.00 | 0.035      | 0.038     | 0.039 |
| b   | 0.30     | 0.32     | 0.45 | 0.012      | 0.013     | 0.018 |
| С   | 0.10     | 0.15     | 0.20 | 0.004      | 0.006     | 0.008 |
| D   | 2.95     | 3.05     | 3.10 | 0.116      | 0.120     | 0.122 |
| Е   | 2.70     | 2.85     | 2.98 | 0.106      | 0.112     | 0.117 |
| E <sub>1</sub>                              | 1.55     | 1.65     | 1.70 | 0.061      | 0.065     | 0.067 |
| е   | 0.95 BSC |          |      | 0.0374 BSC |           |       |
| <b>e</b> <sub>1</sub>                       | 1.80     | 1.90     | 2.00 | 0.071      | 0.075     | 0.079 |
| L   | 0.32     | -        | 0.50 | 0.012      | -         | 0.020 |
| L <sub>1</sub>                              |          | 0.60 Ref |      |            | 0.024 Ref |       |
| L <sub>2</sub>                              | 0.25 BSC |          |      |            | 0.010 BSC |       |
| R   | 0.10     | -        | -    | 0.004      | -         | -     |
| θ   | 0°       | 4°       | 8°   | 0°         | 4°        | 8°    |
| $\theta_1$                                  | 7° Nom   |          |      |            | 7° Nom    |       |
| ECN: C-06593-Rev. I, 18-Dec-06<br>DWG: 5540 |          |          |      |            |           |       |

#### **PAD** Pattern



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# **Recommended Land Pattern For TSOP-5L / TSOP-6L**





TSOP 5L





#### Note

• All dimensions are in inches (millimeter)

| ECN: C22-0860-Rev. B, 24-Oct-2022 |  |
|-----------------------------------|--|
| DWG: 3010                         |  |



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